High Current Transistors

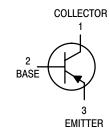
PNP Silicon

- Device Marking: 490
 - 490A 490B



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http://onsemi.com





CASE 29 TO-92 STYLE 17

ORDERING INFORMATION

Device	Package	Shipping
BC490	TO-92	5000 Units/Box
BC490A	TO-92	5000 Units/Box
BC490AZL1	TO-92	2000/Ammo Pack
BC490BZL1	TO-92	2000/Ammo Pack

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	-80	Vdc
Collector-Base Voltage	VCBO	-80	Vdc
Emitter-Base Voltage	VEBO	-4.0	Vdc
Collector Current — Continuous	IC	-1.0	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	TJ, Tstg	–55 to +150	°C

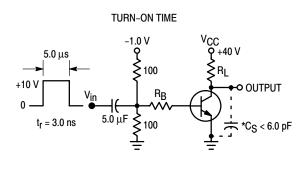
THERMAL CHARACTERISTICS

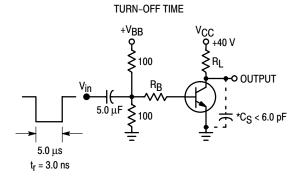
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta}JA$	200	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	83.3	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = -10 \text{ mAdc}, I_B = 0$)	V _(BR) CEO	-80	—	_	Vdc
Collector–Base Breakdown Voltage $(I_{C} = -100 \ \mu Adc, I_{E} = 0)$	V _(BR) CBO	-80	—	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	-4.0	—	_	Vdc
Collector Cutoff Current (V _{CB} = -60 Vdc, I _E = 0)	ICBO	_	—	-100	nAdc
ON CHARACTERISTICS*					
$\begin{array}{l} \mbox{DC Current Gain} \\ (I_C = -10 \mbox{ mAdc}, \mbox{ V}_{CE} = -2.0 \mbox{ Vdc}) \\ (I_C = -100 \mbox{ mAdc}, \mbox{ V}_{CE} = -2.0 \mbox{ Vdc}) \\ & \mbox{ BC490A} \\ & \mbox{ BC490B} \\ \\ (I_C = -1.0 \mbox{ Adc}, \mbox{ V}_{CE} = -5.0 \mbox{ Vdc}) \end{array}$	hfe	40 60 100 160 15	 140 	 400 250 400 	_
Collector–Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$) ($I_C = -1.0 \text{ Adc}$, $I_B = -100 \text{ mAdc}$)	V _{CE(sat)}		-0.25 -0.5	-0.5	Vdc
Base–Emitter Saturation Voltage $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$ $(I_C = -1.0 \text{ Adc}, I_B = -100 \text{ mAdc})$	V _{BE(sat)}		-0.9 -1.0	-1.2	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = –50 mAdc, V _{CE} = –2.0 Vdc, f = 100 MHz)	fT	—	150	_	MHz
Output Capacitance ($V_{CB} = -10$ Vdc, $I_E = 0$, f = 1.0 MHz)	C _{ob}	_	9.0	—	pF
Input Capacitance ($V_{EB} = -0.5 \text{ Vdc}, I_{C} = 0, f = 1.0 \text{ MHz}$)	C _{ib}	_	110	—	pF

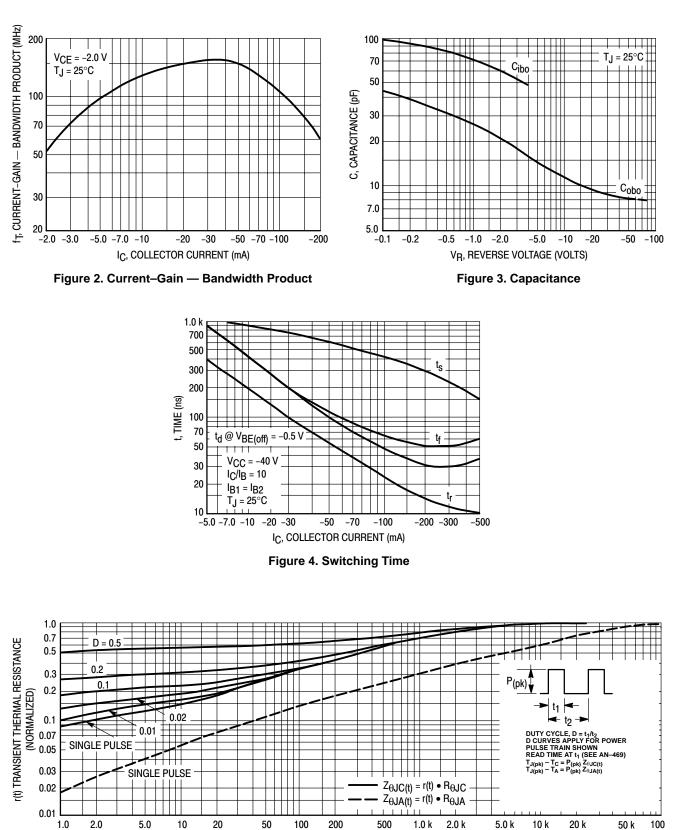
1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle 2%.





*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits



t, TIME (ms) Figure 5. Thermal Response

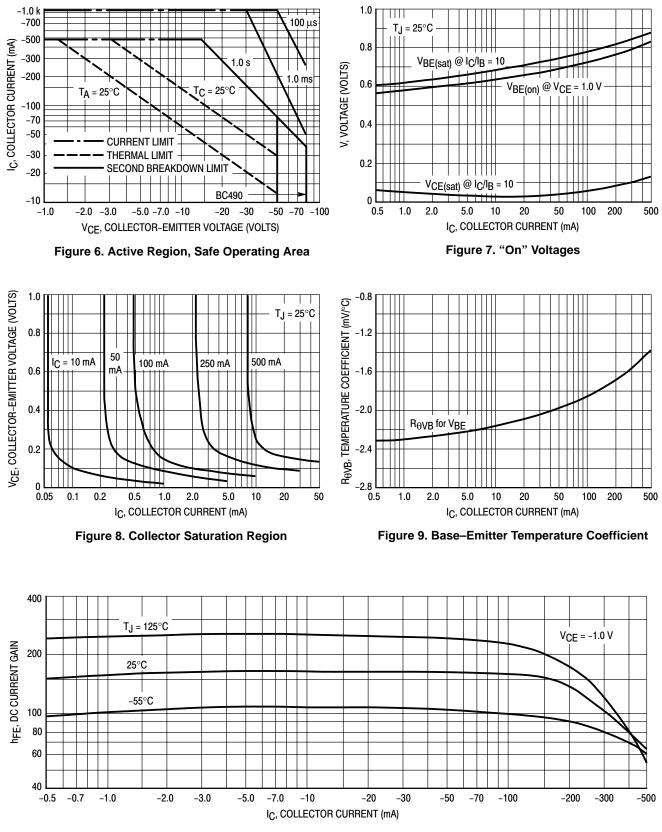


Figure 10. DC Current Gain

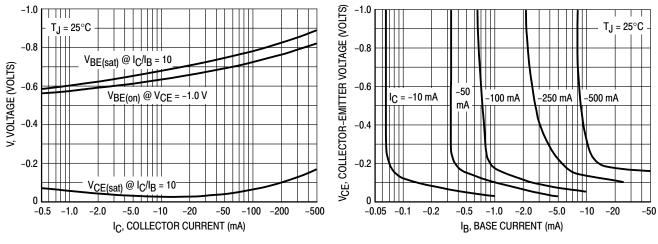


Figure 11. "On" Voltages

Figure 12. Collector Saturation Region

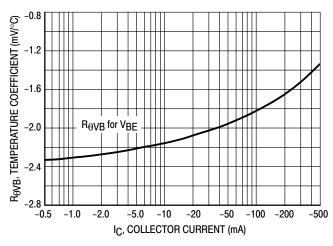
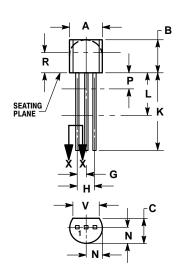


Figure 13. Base–Emitter Temperature Coefficient

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUL OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER

<u>Notes</u>

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